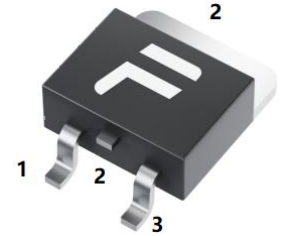


**TO-252-3L Bipolar Transistor 双极型三极管**

■ Features 特点

1.B 2.C 3.E  
PNP High Voltage 高压



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	$V_{CBO}$	-400	V
Collector-Emitter Voltage 集电极发射极电压	$V_{CEO}$	-400	V
Emitter-Base Voltage 发射极基极电压	$V_{EBO}$	-7	V
Collector Current 集电极电流	$I_C$	-0.5	A
Collector Current(Pulse)集电极脉冲电流	$I_{CM}$	-1	A
Power dissipation 耗散功率	$P_C(T_a=25^{\circ}C)$ $(T_C=25^{\circ}C)$	1 10	W
Thermal Resistance Junction-Ambient 热阻 Junction-Case	$R_{\theta JA}$ $R_{\theta JC}$	125 12.5	$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	-55to+150 $^{\circ}C$	

■ Device Marking 产品打标

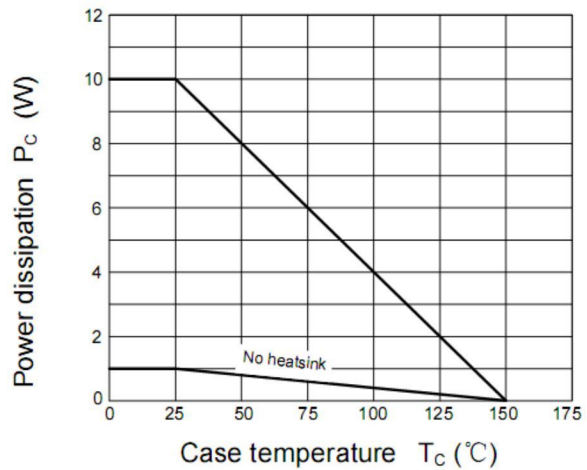
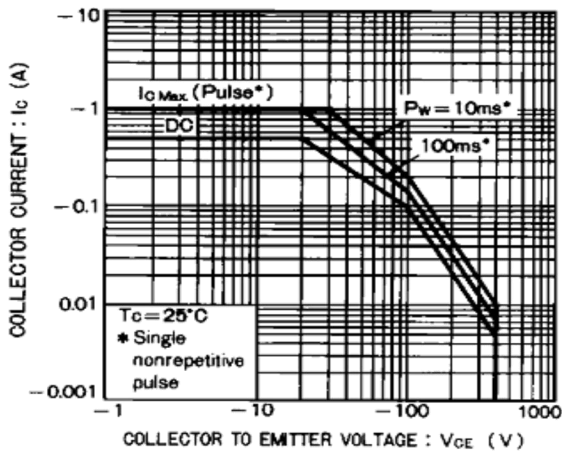
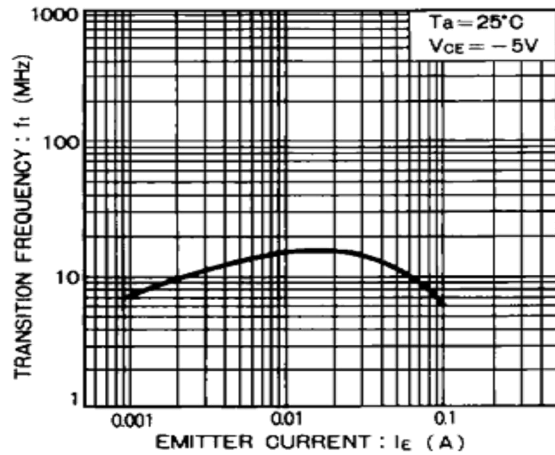
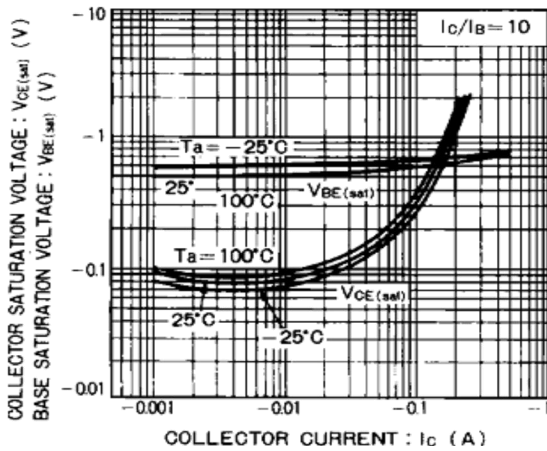
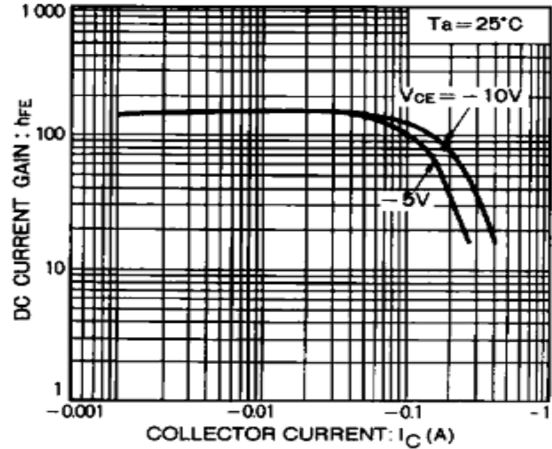
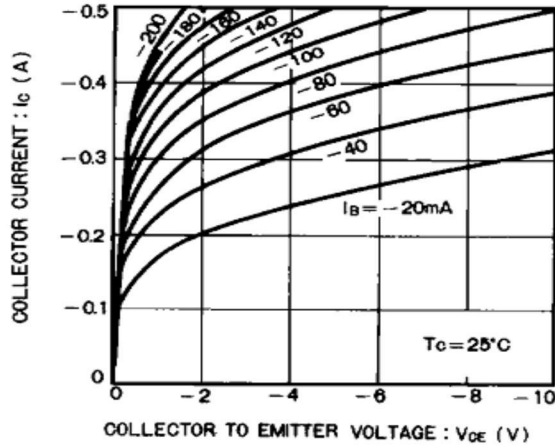
$H_{FE}$	56-120(N)	82-180(P)	120-270(Q)
Mark	2SA1727N	2SA1727P	2SA1727Q

■ **Electrical Characteristics 电特性**

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压( $I_C = -50\mu\text{A}$ , $I_E = 0$ )	$BV_{CBO}$	-400	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压( $I_C = -1\text{mA}$ , $I_B = 0$ )	$BV_{CEO}$	-400	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压( $I_E = -50\mu\text{A}$ , $I_C = 0$ )	$BV_{EBO}$	-7	—	—	V
Collector-Base Leakage Current 集电极基极漏电流( $V_{CB} = -400\text{V}$ , $I_E = 0$ )	$I_{CBO}$	—	—	-10	$\mu\text{A}$
Emitter-Base Leakage Current 发射极基极漏电流( $V_{EB} = -6\text{V}$ , $I_C = 0$ )	$I_{EBO}$	—	—	-10	$\mu\text{A}$
DC Current Gain 直流电流增益( $V_{CE} = -50\text{V}$ , $I_C = -50\text{mA}$ )	$H_{FE}$	56	—	270	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降 ( $I_C = -100\text{mA}$ , $I_B = -10\text{mA}$ )	$V_{CE(sat)}$	—	—	-1	V
Base-Emitter Saturation Voltage 基极发射极饱和压降 ( $I_C = -100\text{mA}$ , $I_B = -10\text{mA}$ )	$V_{BE(sat)}$	—	—	-1.2	V
Transition Frequency 特征频率( $V_{CE} = -5\text{V}$ , $I_C = -50\text{mA}$ )	$f_T$	—	12	—	MHz
Turn On Time 开通时间 ( $V_{CC} = -150\text{V}$ , $R_L = 1.5\text{K}\Omega$ , $I_C = -100\text{mA}$ , $I_{B1} = -I_{B2} = -10\text{mA}$ )	$t_{on}$	—	0.6	—	$\mu\text{s}$
Storage Time 贮存时间 ( $V_{CC} = -150\text{V}$ , $R_L = 1.5\text{K}\Omega$ , $I_C = -100\text{mA}$ , $I_{B1} = -I_{B2} = -10\text{mA}$ )	$t_{stg}$	—	2.7	—	$\mu\text{s}$
Fall Time 下降时间 ( $V_{CC} = -150\text{V}$ , $R_L = 1.5\text{K}\Omega$ , $I_C = -100\text{mA}$ , $I_{B1} = -I_{B2} = -10\text{mA}$ )	$t_f$	—	1.0	—	$\mu\text{s}$
Output Capacitance 输出电容( $V_{CB} = -10\text{V}$ , $I_E = 0$ , $f = 1\text{MHz}$ )	$C_{ob}$	—	18	—	pF

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸

	Min.	Max.	Min.	Max.
A	2.20	2.50	0.087	0.094
A1	1.00	1.40	0.039	0.055
A2	0.00	0.15	0.000	0.006
B	1.00	1.40	0.039	0.055
b	0.50	0.70	0.020	0.028
b1	0.70	0.90	0.028	0.035
c	0.40	0.60	0.016	0.024
c1	0.40	0.60	0.016	0.024
D	6.30	6.70	0.248	0.264
D1	5.10	5.50	0.201	0.217
E	5.30	6.00	0.209	0.236
e	2.20	2.40	0.087	0.094
e1	4.40	4.80	0.173	0.189
L	9.60	10.40	0.378	0.409
L1	0.60	1.00	0.024	0.039
L2	1.40	1.70	0.055	0.063